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Data Sheet November 2013

15 A, 400 V - 600 V, Hyperfast Diode

The RHRP1540, RHRP1560 is a hyperfast diode with soft recovery characteristics. It has the half recovery time of ultrafast diodes and is silicon nitride passivated ionimplanted epitaxial planar construction. These devices are intended to be used as freewheeling/ clamping diodes and diodes in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PART NUMBER	PACKAGE	BRAND		
RHRP1540	TO-220AC-2L	RHRP1540		
RHRP1560	TO-220AC-2L	RHRP1560		

NOTE: When ordering, use the entire part number.

Symbol



Features

- Hyperfast Recovery t_{rr} = 40 ns (@ I_F = 15 A)
- Max Forward Voltage, V_F = 2.1 V (@ T_C = 25°C)
- 400 V, 600 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- RoHS Compliant

Applications

- Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Packaging

JEDEC TO-220AC



Absolute Maximum Ratings T _C = 25°C, Unless Otherwise Specified			
	RHRP1540	RHRP1560	UNIT
Peak Repetitive Reverse Voltage	400	600	V
Working Peak Reverse Voltage	400	600	V
DC Blocking VoltageV _R	400	600	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 140^{\circ}C$)	15	15	А
Repetitive Peak Surge Current	30	30	Α
Nonrepetitive Peak Surge Current	200	200	Α
Maximum Power Dissipation	100	100	W
Avalanche Energy (See Figures 10 and 11)	20	20	mJ
Operating and Storage Temperature	-65 to 175	-65 to 175	οС

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RHRP1540		RHRP1560				
		MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V _F	I _F = 15 A	-	-	2.1	-	-	2.1	V
	I _F = 15 A, T _C = 150 ^o C	-	-	1.7	-	-	1.7	V
I _R	V _R = 400 V	-	-	100	-	-	-	μА
	V _R = 600 V	-	-	-	-	-	100	μА
	$V_R = 400 \text{ V}, T_C = 150^{\circ}\text{C}$	-	-	500	-	-	-	μА
	$V_R = 600 \text{ V}, T_C = 150^{\circ}\text{C}$	-	-	-	-	-	500	μА
T _{rr}	I _F = 1 A, dI _F /dt = 100 A/μs	-	-	35	-	-	35	ns
	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	-	40	-	-	40	ns
t _a	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	20	-	-	20	-	ns
t _b	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	15	-	-	15	-	ns
Q _{rr}	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	40	-	-	40	-	nC
CJ	V _R = 10 V, I _F = 0 A	-	60	-	-	60	-	pF
$R_{ heta JC}$		-	-	1.5	-	-	1.5	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

 I_R = Instantaneous reverse current .

 T_{rr} = Reverse recovery time (See Figure 9), summation of $t_a + t_b$.

ta = Time to reach peak reverse current (See Figure 9).

 t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 9).

Q_{rr} = Reverse Recovery Change.

C_J = Junction Capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse Width.

D = Duty Cycle.

Typical Performance Curves

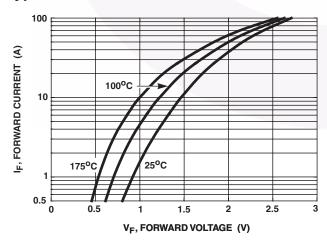


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

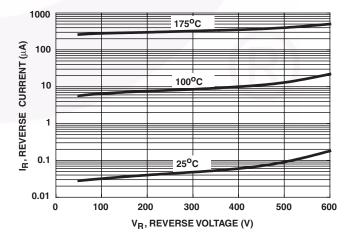


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

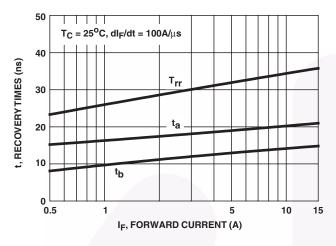


FIGURE 3. T_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

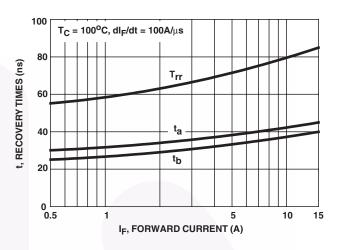


FIGURE 4. T_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

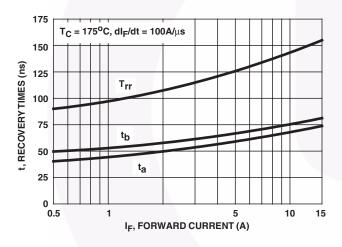


FIGURE 5. T_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

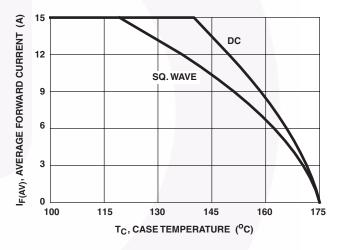


FIGURE 6. CURRENT DERATING CURVE

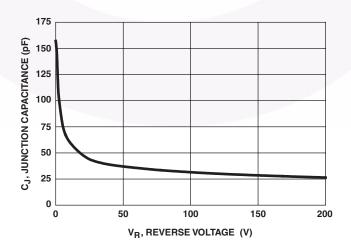


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuits and Waveforms

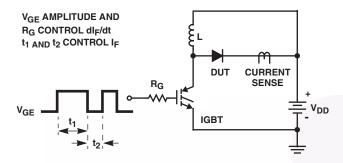


FIGURE 8. T_{rr} TEST CIRCUIT

 $I_{MAX} = 1A$ L = 40mH $R < 0.1\Omega$ $E_{AVL} = 1/2Li^2 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right]$ $Q_1 = IGBT \left(BV_{CES} > DUT V_{R(AVL)} \right)$ Q_1 V_{DD} V_{DD} V_{DD}

FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

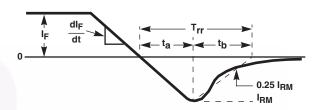


FIGURE 9.Tt_{rr} WAVEFORMS AND DEFINITIONS

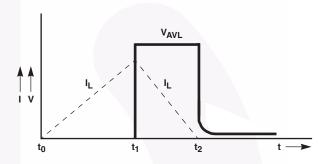
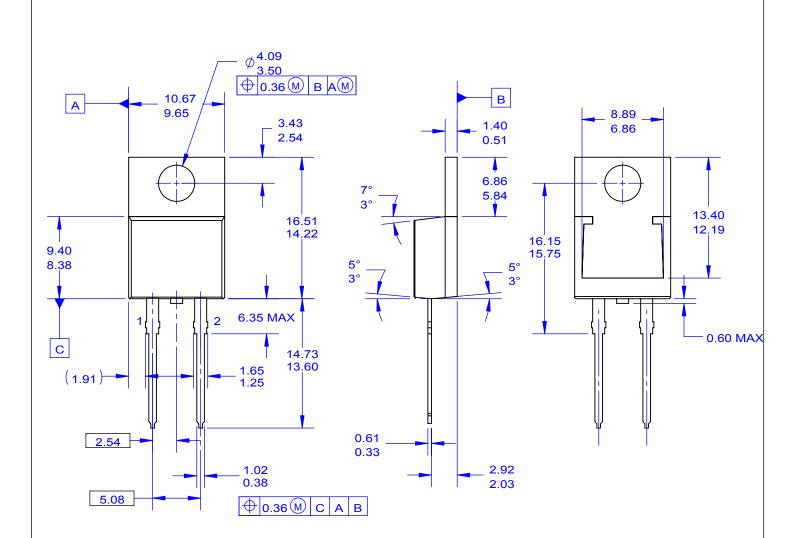
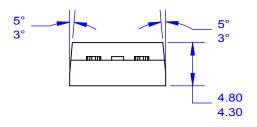


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS







NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DRAWING FILE NAME: TO220A02REV5

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